Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

Claims 1-109 (Canceled).

110. (Currently Amended): A method for plating a film to a desired thickness on a surface of a substrate, the substrate being a wafer used in integrated circuit fabrication, the method comprising:

rotating the substrate about a center-point;

flowing an electrolyte solution directly on the surface of the substrate as the substrate is rotated;

plating the film to the desired thickness on a first portion of the substrate surface; and

plating the film to the desired thickness on at least a second portion of the substrate surface at a different radial location than the first portion to give a film at the desired thickness on the substrate.

111. (Withdrawn): The method of claim 110, wherein the desired thickness is for a layer of the film on the substrate.

112. (Withdrawn): The method of claim 111, further comprising:

plating an additional thickness on the layer to give a film of a second uniform thickness greater than the desired thickness of the layer on the substrate.

113. (Withdrawn): The method of claim 112, wherein the film is plated on the first portion of the substrate by flowing an electrolyte on the first portion of the substrate surface and applying a plating current to plate the film on the first portion of the substrate until the film reaches the desired thickness; repeating the electrolyte flowing and plating current applying for at least the second portion of the substrate to plate the film on the second portion to the desired thickness; and flowing an electrolyte to the first portion and the second portion of the substrate and applying plating current to at least the second portion until the second uniform thickness is obtained.

114. (Withdrawn): The method of claim 113, wherein the film is plated on the first and second portions of the substrate by independently providing the plating current to plating electrodes for the first and second portions.

115. (Withdrawn): The method of claim 114, wherein the electrolyte is independently flowed to the first and second portions of the substrate.

116. (Currently Amended): The method of claim 110, wherein the film is plated on the first and the second ~~portion~~ portions of the substrate by flowing an electrolyte on the first and the second ~~portion~~ portions of the substrate simultaneously, and applying plating current to plating electrodes for the first and second portions separately.

117. (Previously Presented): The method of claim 116, further comprising providing said plating current to the first portion of the substrate to prevent deplating after the film reaches the desired thickness on the first portion of the substrate while applying said plating current to the second portion of the substrate.

118. (Previously Presented): The method of claim 116, further comprising providing plating voltage to the second portion of the substrate to prevent deplating while applying said plating current to the first portion of the substrate.

119. (Previously Presented): The method of claim 116, further comprising moving the first portion of the substrate out of the electrolyte after the film reaches the desired thickness on the first portion of the substrate while applying the plating current to the second portion of the substrate.

120. (Withdrawn): The method of claim 110, wherein said film is plated on the first portion and the second portion of the substrate by flowing an electrolyte on the first portion of the substrate while plating the film on the first portion of the substrate; and by flowing electrolyte to the first portion and second portion of the substrate simultaneously, while plating the film on the second portion of the substrate.

121. (Withdrawn): The method of claim 120, further comprising providing a plating voltage to the first portion of the substrate to prevent deplating after the film reaches the desired thickness on the first portion of the substrate while applying the plating current to the second portion of the substrate.

122. (Withdrawn): The method of claim 110, wherein said film is plated on the first and the second ~~portion~~ portions of the substrate by flowing an electrolyte on the first portion of the substrate by moving a movable jet anode proximate the first portion of substrate; and by flowing an electrolyte on the second portion of the substrate by moving a movable jet anode proximate the second portion of the substrate.

123. (Withdrawn): The method of claim 110, further comprising immersing the substrate surface into an electrolyte, and plating the film on the first portion and the second portion of the substrate by separately moving a movable jet anode proximate the first portion of substrate and moving a movable jet anode proximate the second portion of the substrate.

124. (Withdrawn): The method of claim 110, wherein the film is plated on the first portion of the substrate while the film is plated on the second portion of the substrate.

125. (Withdrawn): The method of claim 124, wherein the film is plated on the first portion and the second portion of the substrate by flowing an electrolyte on the first portion of the substrate

while plating the film on the first portion of the substrate, and by flowing electrolyte to the first portion and second portion of the substrate simultaneously while plating the film on the first portion and the second portion of the substrate simultaneously.

126. (Withdrawn): The method of claim 125, wherein the film is plated on the first portion and second portion of the substrate to the desired thickness to give a layer, further comprising:

plating an additional thickness on the layer to give a film of a second uniform thickness greater than the desired thickness of the layer on the substrate.

127. (Withdrawn): The method of claim 110, wherein the film is plated on the first portion and the second portion of the substrate by flowing an electrolyte on the first portion of the substrate while plating the film on the first portion of the substrate, and by flowing an electrolyte to the first and second ~~portion~~ portions of the substrate simultaneously while plating the film on the second portion of the substrate.

128. (Withdrawn): The method of claim 127, further comprising providing a plating voltage to the first portion of the substrate to prevent deplating after the film reaches the desired thickness on the first portion of the substrate while applying a plating current to the second portion of substrate.

129. (Withdrawn): The method of claim 128, wherein the film is plated on the first portion and second portion of the substrate to the desired thickness to give a layer, further comprising:

plating an additional thickness on the layer to give a film of a second uniform thickness grater than the desired thickness of the layer on the substrate.

130. (Withdrawn): The method of claim 110, wherein the second portion of the substrate is adjacent to the first portion of the substrate.

131. (Withdrawn): The method of claim 110, wherein the substrate is a semiconductor wafer.

132. (Withdrawn): The method of claim 131, wherein the semiconductor wafer is a silicon wafer.

133. (Withdrawn): The method of claim 132, wherein the silicon wafer includes a barrier layer on its top.

134. (Withdrawn): The method of claim 133, wherein the barrier layer is one of titanium, titanium nitride, tantalum or tantalum nitride.

135. (Withdrawn): The method of claim 133, wherein the semiconductor wafer further includes a seed layer on top of the barrier layer.

136. (Withdrawn): The method of claim 135, the seed layer being thicker proximate a peripheral portion and thinner at an inner portion of the semiconductor wafer.

137. (Withdrawn): The method of claim 131, wherein the film comprises interconnects in integrated circuits on the semiconductor wafer.

138. (Withdrawn): The method of claim 137, wherein the interconnects are in a damascene structure.

139. (New): A method for plating a film to a desired thickness on a surface of a wafer used in integrated circuit fabrication, the method comprising:

rotating the wafer about a center-point;

flowing an electrolyte solution directly on the surface of the wafer as the wafer is rotated;

plating the film to the desired thickness on a first portion of the wafer surface at a first radial location on the wafer; and

plating the film to the desired thickness on at least a second portion of the wafer surface at a second radial location different from the first portion to give a film at the desired thickness on the wafer.

140. (New): The method of claim 139, wherein the film is plated on the first portion of the wafer by flowing an electrolyte on the first portion of the wafer surface and applying a plating current to plate the film on the first portion of the wafer until the film reaches the desired thickness; repeating the electrolyte flowing and plating current applying for at least the second portion of the wafer to plate the film on the second portion to the desired thickness; and flowing an electrolyte to the first portion and the second portion of the wafer and applying plating current to at least the second portion until a second uniform thickness is obtained.

141. (New): The method of claim 140, wherein the film is plated on the first and second portions of the wafer by independently providing the plating current to plating electrodes for the first and second portions.

142. (New): The method of claim 141, wherein the electrolyte is independently flowed to the first and second portions of the wafer.

143. (New): The method of claim 139, wherein the film is plated on the first and the second portions of the wafer by flowing an electrolyte on the first and the second portions of the wafer simultaneously, and applying plating current to plating electrodes for the first and second portions separately.

144. (New): The method of claim 143, further comprising providing said plating current to the first portion of the wafer to prevent deplating after the film reaches the desired thickness on the first portion of the wafer while applying said plating current to the second portion of the wafer.

145. (New): The method of claim 143, further comprising providing plating voltage to the second portion of the wafer to prevent deplating while applying said plating current to the first portion of the wafer.

146. (New): The method of claim 143, further comprising moving the first portion of the wafer out of the electrolyte after the film reaches the desired thickness on the first portion of the wafer while applying the plating current to the second portion of the wafer.

147. (New): The method of claim 143, wherein said film is plated on the first portion and the second portion of the wafer by flowing an electrolyte on the first portion of the wafer while plating the film on the first portion of the wafer; and by flowing electrolyte to the first portion and second portion of the wafer simultaneously, while plating the film on the second portion of the wafer.

148. (New): The method of claim 147, further comprising providing a plating voltage to the first portion of the wafer to prevent deplating after the film reaches the desired thickness on the first portion of the wafer while applying the plating current to the second portion of the wafer.

149. (New): The method of claim 139, wherein the film is plated on the first portion of the wafer while the film is plated on the second portion of the wafer.

150. (New): The method of claim 149, wherein the film is plated on the first portion and the second portion of the wafer by flowing an electrolyte on the first portion of the wafer while plating the film on the first portion of the wafer, and by flowing electrolyte to the first portion and second portion of the wafer simultaneously while plating the film on the first portion and the second portion of the wafer simultaneously.

151. (New): The method of claim 150, wherein the film is plated on the first portion and second portion of the wafer to the desired thickness to give a layer, further comprising:

plating an additional thickness on the layer to give a film of a second uniform thickness greater than the desired thickness of the layer on the wafer.

152. (New): The method of claim 139, wherein the film is plated on the first portion and the second portion of the wafer by flowing an electrolyte on the first portion of the wafer while plating the film on the first portion of the wafer, and by flowing an electrolyte to the first and second portion of the wafer simultaneously while plating the film on the second portion of the wafer.

153. (New): The method of claim 152, further comprising providing a plating voltage to the first portion of the wafer to prevent deplating after the film reaches the desired thickness on the first portion of the wafer while applying a plating current to the second portion of wafer.

154. (New): The method of claim 153, wherein the film is plated on the first portion and second portion of the wafer to the desired thickness to give a layer, further comprising:

plating an additional thickness on the layer to give a film of a second uniform thickness grater than the desired thickness of the layer on the wafer.

155. (New): The method of claim 139, wherein the second portion of the wafer is adjacent to the first portion of the wafer.

156. (New): The method of claim 139, wherein the wafer further includes a seed layer on top of a barrier layer.

157. (New): A method for plating a film to a desired thickness on a surface of a wafer used in integrated circuit fabrication, the method comprising:

rotating the wafer about a center-point;

flowing an electrolyte solution on the surface of the wafer as the wafer is rotated;

plating the film to the desired thickness on a first portion of the wafer surface at a first radial location on the wafer; and

plating the film to the desired thickness on at least a second portion of the wafer surface at a second radial location different from the first portion,

wherein the film is plated on the first and the second portions of the wafer by flowing the electrolyte on the first and the second portions of the wafer simultaneously, and applying plating current to plating electrodes for the first and second portions separately.

158. (New): The method of claim 157, further comprising providing said plating current to the first portion of the wafer to prevent deplating after the film reaches the desired thickness on the first portion of the wafer while applying said plating current to the second portion of the wafer.

159. (New): The method of claim 157, further comprising providing plating voltage to the second portion of the wafer to prevent deplating while applying said plating current to the first portion of the wafer.